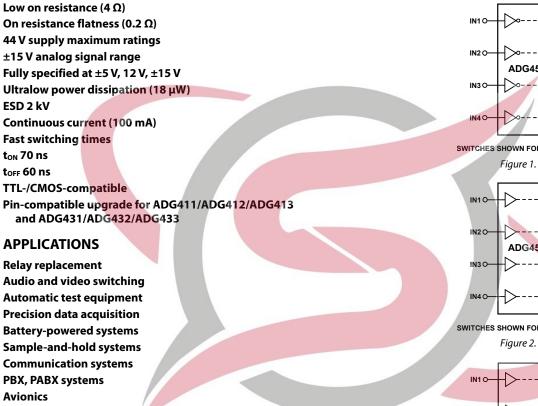


**FEATURES** 

 $LC^{2}MOS$ 5  $\Omega$  R<sub>on</sub> SPST Switches ADG451/ADG452/ADG453

#### FUNCTIONAL BLOCK DIAGRAMS



#### **GENERAL DESCRIPTION**

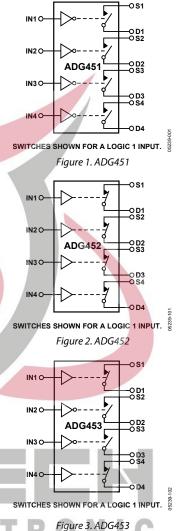
The ADG451/ADG452/ADG453 are monolithic CMOS devices comprising four independently selectable switches. They are designed on an enhanced LC<sup>2</sup>MOS process that provides low power dissipation yet gives high switching speed and low on resistance.

The on resistance profile is very flat over the full analog input range, ensuring excellent linearity and low distortion when switching audio signals. Fast switching speed, coupled with high signal bandwidth, makes the parts suitable for video signal switching. CMOS construction ensures ultralow power dissipation, making the parts ideally suited for portable and batterypowered instruments.

The ADG451/ADG452/ADG453 contain four independent, single-pole/single-throw (SPST) switches. The ADG451 and ADG452 differ only in that the digital control logic is inverted. The ADG451 switches are turned on with a logic low on the appropriate control input, while a logic high is required for the ADG452.

#### Rev. C

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The ADG453 has two switches with digital control logic similar to that of the ADG451, while the logic is inverted on the other two switches.

Each switch conducts equally well in both directions when on, and each has an input signal range that extends to the supplies. In the off condition, signal levels up to the supplies are blocked.

The ADG453 exhibits break-before-make switching action for use in multiplexer applications. Inherent in the design is low charge injection for minimum transients when switching the digital inputs.

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## **PRODUCT HIGHLIGHTS**

- 1. Low  $R_{\rm ON}$  (5  $\Omega$  maximum).
- 2. Ultralow Power Dissipation.
- 3. Extended Signal Range.

The ADG451/ADG452/ADG453 are fabricated on an enhanced LC<sup>2</sup>MOS process, giving an increased signal range that fully extends to the supply rails.

4. Break-Before-Make Switching. This prevents channel shorting when the switches are configured as a multiplexer (ADG453 only.) 5. Single-Supply Operation.

For applications in which the analog signal is unipolar, the ADG451/ADG452/ADG453 can be operated from a single rail power supply. The parts are fully specified with a single 12 V power supply and remain functional with single supplies as low as 5.0 V.

6. Dual-Supply Operation.

For applications where the analog signal is bipolar, the ADG451/ADG452/ADG453 can be operated from a dual power supply ranging from  $\pm 4.5$  V to  $\pm 20$  V.



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## **SPECIFICATIONS**

### **15 V DUAL SUPPLY**

 $V_{DD}$  = 15 V,  $V_{SS}$  = -15 V,  $V_L$  = 5 V, GND = 0 V. All specifications  $T_{MIN}$  to  $T_{MAX}$ , unless otherwise noted. **Table 1.** 

	B	lersion <sup>1</sup>		
Parameter	25°C	T <sub>MIN</sub> to T <sub>MAX</sub>	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		$V_{\text{SS}}$ to $V_{\text{DD}}$	V	
On Resistance (R <sub>ON</sub> )	4		Ωtyp	$V_D = -10 V$ to $+10 V$ , $I_S = -10 mA$
	5	7	Ωmax	
On Resistance Match Between Channels (ΔR <sub>on</sub> )	0.1		Ωtyp	$V_D = \pm 10 \text{ V}, \text{ I}_S = -10 \text{ mA}$
	0.5	0.5	Ωmax	
On Resistance Flatness (R <sub>FLAT(ON)</sub> )	0.2		Ω typ	$V_D = -5 V, 0 V, +5 V, I_S = -10 mA$
	0.5	0.5	Ωmax	
LEAKAGE CURRENTS <sup>2</sup>				
Source Off Leakag <mark>e, Is (OF</mark> F)	±0.02		nA typ	$V_{D} = \pm 10 \text{ V}, \text{ V}_{\text{S}} = \pm 10 \text{ V}; \text{ see Figure 17}$
	±0.5	±2.5	nA max	
Drain Off Leakage, I <sub>D</sub> (OFF)	±0.02		nA typ	$V_D = \pm 10 \text{ V}, V_S = \pm 10 \text{ V};$ see Figure 17
	±0.5	±2.5	nA max	
Channel On Leakage, I <sub>D</sub> , I <sub>s</sub> (ON)	±0.04		nA typ	$V_D = V_S = \pm 10 V$ ; see Figure 18
	±1	±5	nA max	
DIGITAL INPUTS				
Input High Voltage, VINH		2.4	V min	
Input Low Voltage, V <sub>INL</sub>		0.8	V max	
Input Current, I <sub>INL</sub> or I <sub>INH</sub>	0.005		µA typ	$V_{IN} = V_{INL}$ or $V_{INH}$ ; all others = 2.4 V or 0.8 V, respectively
		±0.5	µA max	
DYNAMIC CHARACTERISTICS <sup>3</sup>				
ton	70		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$ , $V_S = \pm 10 V$ ; see Figure 19
	180	220	ns max	
toff	60		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$ , $V_S = \pm 10 V$ ; see Figure 19
	140	180	ns max	
Break-Before-Make Time Delay, t <sub>D</sub> (ADG453 Only)	15		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$ , $V_{S1} = V_{S2} = +10 V$ ; see Figure 20
	5	5	ns min	
Charge Injection	20		pC typ	$V_s = 0 V$ , $R_s = 0 \Omega$ , $C_L = 1.0 nF$ ; see Figure 21
	30		pC max	
Off Isolation	65		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 22
Channel-to-Channel Crosstalk	-90		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 23
Cs (OFF)	37		pF typ	f=1MHz D O N C
C <sub>D</sub> (OFF)	37		pF typ	f=1MHz <b>NUNIU</b>
C <sub>D</sub> , C <sub>s</sub> (ON)	140		pF typ	f = 1 MHz
POWER REQUIREMENTS				$V_{DD} = 16.5 V$ , $V_{SS} = -16.5 V$ ; digital inputs = 0 V or 5 V
l <sub>DD</sub>	0.0001		μA typ	
	0.5	5	µA max	
lss	0.0001		μA typ	
	0.5	5	µA max	
lı.	0.0001		μA typ	
	0.5	5	µA max	
Ignd <sup>3</sup>	0.0001		μA typ	
	0.5	5	µA max	

<sup>1</sup> Temperature range for B version is  $-40^{\circ}$ C to  $+85^{\circ}$ C.

 $^{2}$  T<sub>MAX</sub> = 70°C.

<sup>3</sup> Guaranteed by design, not subject to production test.

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#### **12 V SINGLE SUPPLY**

 $V_{DD}$  = 12 V,  $V_{SS}$  = 0 V,  $V_L$  = 5 V, GND = 0 V. All specifications  $T_{MIN}$  to  $T_{MAX}$ , unless otherwise noted.

#### Table 2.

<b>B</b> Version <sup>1</sup>					
Parameter	25°C	$T_{\text{MIN}}$ to $T_{\text{MAX}}$	Unit	Test Conditions/Comments	
ANALOG SWITCH					
Analog Signal Range		$0 V to V_{\text{DD}}$	V		
On Resistance (Ron)	6		Ω typ	$V_D = 0 V to + 10 V$ , $I_S = -10 mA$	
	8	10	Ωmax		
On Resistance Match Between Channels ( $\Delta R_{ON}$ )	0.1		Ω typ	$V_D = 10 V$ , $I_S = -10 mA$	
	0.5	0.5	Ωmax		
On Resistance Flatness (R <sub>FLAT(ON)</sub> )	1.0	1.0	Ωtyp	$V_D = 0 V, 5 V, I_S = -10 mA$	
LEAKAGE CURRENTS <sup>2, 3</sup>					
Source Off Leakage, Is (OFF)	±0.02		nA typ	$V_{D} = 0 V$ , 10 V, $V_{S} = 0 V$ , 10 V; see Figure 17	
	±0.5	<b>±2</b> .5	nA max		
Drain Off Lea <mark>kage, I</mark> D (OFF)	±0.02		nA typ	$V_{\rm D} = 0 V$ , 10 V, $V_{\rm S} = 0 V$ , 10 V; see Figure 17	
	±0.5	±2.5	nA max		
Channel On Leakage, I <sub>D</sub> , I <sub>S</sub> (ON)	±0.04		nA typ	$V_{D} = V_{S} = 0 V$ , 10 V; see Figure 18	
	±1	±5	nA max		
DIGITAL INPUTS			1		
Input High Voltage, VINH		2.4	Vmin		
Input Low Voltage, VINL		0.8	V max		
Input Current, I <sub>INL</sub> or I <sub>INH</sub>	0.005		µA typ	V <sub>IN</sub> = V <sub>INL</sub> or V <sub>INH</sub>	
		±0.5	µA max		
DYNAMIC CHARACTERISTICS <sup>4</sup>					
ton	100		ns typ	$R_{L} = 300 \Omega, C_{L} = 35 pF, V_{s} = 8 V; see Figure 19$	
	220	260	ns max		
toff	80		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$ , $V_S = 8 V$ ; see Figure 19	
	160	200	ns max		
Break-Before-Make Time Delay, t₀ (ADG453 Only)	15		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$ , $V_{s1} = V_{s2} = 8 V$ ;	
				see Figure 20	
	10	10	ns min		
Charge Injection	10		pC typ	$V_s = 6 V$ , $R_s = 0 \Omega$ , $C_L = 1.0 nF$ ; see Figure 21	
Channel-to-Channel Crosstalk	-90		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 23	
Cs (OFF)	60		pF typ	f = 1 MHz	
C <sub>D</sub> (OFF)	60		pF typ	f = 1 MHz	
C <sub>D</sub> , C <sub>s</sub> (ON)	100		pF typ	f = 1 MHz	
POWER REQUIREMENTS				$V_{DD} = 13.2 \text{ V}; \text{ digital inputs} = 0 \text{ V or } 5 \text{ V}$	
IDD	0.0001		μA typ	BONIC	
	0.5	5	µA max		
l,	0.0001	-	μA typ		
-	0.5	5	µA max	$V_{L} = 5.5 V$	
	0.0001	-	μA typ		
	0.0001		1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1		

<sup>1</sup> Temperature range for B version is  $-40^{\circ}$ C to  $+85^{\circ}$ C.

<sup>3</sup> Tested with dual supplies.

<sup>4</sup> Guaranteed by design, not subject to production test.

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 $<sup>^{2}</sup>$  T<sub>MAX</sub> = 70°C.

#### **5 V DUAL SUPPLY**

 $V_{DD}$  = +5 V,  $V_{SS}$  = -5 V,  $V_L$  = +5 V, GND = 0 V. All specifications  $T_{MIN}$  to  $T_{MAX}$ , unless otherwise noted.

#### Table 3.

	BV	ersion <sup>1</sup>			
Parameter	25°C T <sub>MIN</sub> to T <sub>MAX</sub>		Unit	Test Conditions/Comments	
ANALOG SWITCH					
Analog Signal Range		$V_{\text{SS}}$ to $V_{\text{DD}}$	V		
On Resistance (R <sub>ON</sub> )	7		Ωtyp	$V_D = -3.5$ V to $+3.5$ V, $I_S = -10$ mA	
	12	15	Ωmax		
On Resistance Match Between Channels ( $\Delta R_{ON}$ )	0.3		Ωtyp	$V_D = 3.5 V$ , $I_S = -10 mA$	
	0.5	0.5	Ωmax		
LEAKAGE CURRENTS <sup>2, 3</sup>					
Source Off Leakage, Is (OFF)	±0.02		nA typ	$V_D = \pm 4.5$ , $V_S = \pm 4.5$ ; see Figure 17	
	±0.5	±2.5	nA max		
Drain Off Leakage <mark>, I<sub>D</sub> (OF</mark> F)	±0.02		nA typ	$V_D = 0 V, 5 V, V_S = 0 V, 5 V;$ see Figure 17	
	±0.5	±2.5	nA max		
Channel On Leaka <mark>ge, I<sub>D</sub>, Is</mark> (ON)	±0.04		nA typ	$V_D = V_S = 0 V$ , 5 V; see Figure 18	
	±1	±5	nA max		
DIGITAL INPUTS					
Input High Voltage, VINH		2.4	V min		
Input Low Voltage, VINL		0.8	V max		
Input Current, I <sub>INL</sub> or I <sub>INH</sub>	0.005		μA typ	$V_{IN} = V_{INL} \text{ or } V_{INH}$	
		±0.5	μA max		
DYNAMIC CHARACTERISTICS <sup>4</sup>					
ton	160		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$ , $V_S = 3 V$ ; see Figure 19	
	220	300	ns max		
toff	60		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$ , $V_S = 3 V$ ; see Figure 19	
	140	180	ns max		
Break-Before-Make Time Delay, t <sub>D</sub> (ADG453 Only)	50		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$ , $V_{S1} = V_{S2} = 3 V$ ; see Figure 20	
	5	5	ns min		
Charge Injection	10		pC typ	$V_s = 0 V$ , $R_s = 0 \Omega$ , $C_L = 1.0 nF$ ; see Figure 21	
Off Isolation	65		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 22	
Channel-to-Channel Crosstalk	-76		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 23	
Cs (OFF)	48		pF typ	f = 1 MHz	
C <sub>D</sub> (OFF)	48		pF typ	f = 1 MHz	
C <sub>D</sub> , C <sub>s</sub> (ON)	148		pF typ	f = 1 MHz	
POWER REQUIREMENTS				$V_{DD} = 5.5 V$ ; digital inputs = 0 V or 5 V	
loo	0.0001		μA typ		
	0.5	5 E	μA max	CTRONIC	
lss	0.0001		μA typ		
	0.5	5	µA max		
lı.	0.0001		μA typ		
	0.5	5	µA max	$V_L = 5.5 V$	
Ignd <sup>4</sup>	0.0001		μA typ		
	0.5	5	µA max	$V_L = 5.5 V$	

<sup>1</sup> Temperature range for B version is  $-40^{\circ}$ C to  $+85^{\circ}$ C.

 $^{2}$  T<sub>MAX</sub> = 70°C. <sup>3</sup> Tested with dual supplies.

<sup>4</sup> Guaranteed by design, not subject to production test.

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Stresses above those listed under Absolute Maximum Ratings

## **ABSOLUTE MAXIMUM RATINGS**

 $T_A = 25^{\circ}C$ , unless otherwise noted.

#### Table 4.

ParametersRatingsmay cause permanent damage to the device. This is a stressV_DD to Vss44 Vrating only; functional operation of the device at these or anyV_DD to GND-0.3 V to +32 Vother conditions above those listed in the operational sectionsVss to GND+0.3 V to -32 Vof this specification is not implied. Exposure to absoluteVL to GND-0.3 V to VDD + 0.3 Vmaximum rating conditions for extended periods may affect
VDD to GND-0.3 V to +32 Vother conditions above those listed in the operational sectionsVSS to GND+0.3 V to -32 Vof this specification is not implied. Exposure to absolute
V <sub>55</sub> to GND +0.3 V to -32 V of this specification is not implied. Exposure to absolute
manimum runng contantono for extended periodo may affect
Analog, Digital Inputs <sup>1</sup> $V_{SS} - 2V$ to $V_{DD} + 2V$ or 30 mA, device reliability. whichever occurs first
Continuous Current, S or D 100 mA Only one absolute maximum rating may be applied at any one
Peak Current, S or D (pulsed at 300 mA time. 1 ms, 10% duty cycle maximum)
Operating Temperature Range
Industrial (B Version) –40°C to +85°C ESD CAUTION
Storage Temperature Range -65°C to +150°C ESD (electrostatic discharge) sensitive device.
Junction Temperature 150°C Charged devices and circuit boards can discharge
Plastic DIP Package, Power Dissipation 470 mW without detection. Although this product features patented or proprietary protection circuitry, damage
θ <sub>JA</sub> Thermal Impedance 117°C/W may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to
Lead Temperature, Soldering (10 sec) 260°C avoid performance degradation or loss of functionality.
SOIC Package, Power Dissipation 600 mW
θ <sub>JA</sub> Thermal Impedance 77°C/W
TSSOP Package, Power Dissipation 450 mW
θ <sub>JA</sub> Thermal Impedance 115°C/W
θ <sub>JC</sub> Thermal Impedance 35°C/W
Lead Temperature, Soldering
Vapor Phase (60 sec) 215°C
Infrared (15 sec) 220°C
ESD 2 kV

<sup>1</sup> Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.



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## **PIN CONFIGURATION AND FUNCTION DESCRIPTIONS**

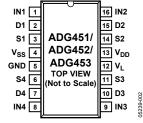


Figure 4. Pin Configuration

#### **Table 5. Pin Function Descriptions**

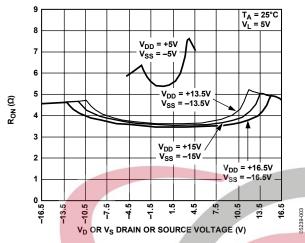
Pin No.	Mnemonic	Description
1	IN1	Logic Control Input.
2	D1	Drain Terminal. Can be an input or an output.
3	S1	Source Terminal. Can be an input or an output.
4	Vss	Most Negative Power Supply Potential in Dual Supplies. In single-supply applications, it can be connected to GND.
5	GND	Ground (0 V) Reference.
6	S4	Source Terminal. Can b <mark>e an input</mark> or an output.
7	D4	Drain Terminal. Can be an input or an output.
8	IN4	Logic Control Input.
9	IN3	Logic Control Input.
10	D3	Drain Terminal. Can be an input or an output.
11	S3	Source Terminal. Can be an input or an output.
12	VL	Logic Power Supply (5 V).
13	V <sub>DD</sub>	Most Positive Power Supply Potential.
14	S2	Source Terminal. Can be an input or an output.
15	D2	Drain Terminal. Can be an input or an output.
16	IN2	Logic Control Input.

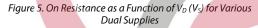
#### Table 6 Truth Table (ADG451/ADG452)

Table 6. Truth	Table (ADG451/AI	)G452)	Table 7	Table 7. Truth Table (ADG453)		
ADG451 In	ADG452 In	Switch Condition	Logic	Switch 1, Switch 4	Switch 2, Switch 3	
0	1	On	0	Off	On	
1	0	Off	1	On	Off	
	S		ELI	ECTRO	NIC	

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## **TYPICAL PERFORMANCE CHARACTERISTICS**





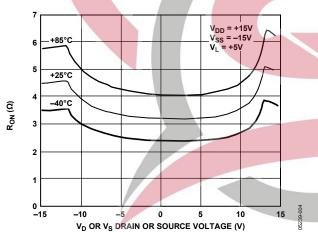


Figure 6. On Resistance as a Function of  $V_D(V_S)$  for Different Temperatures with Dual Supplies

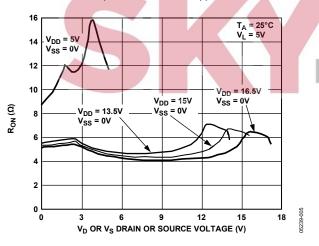


Figure 7. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Various Single Supplies

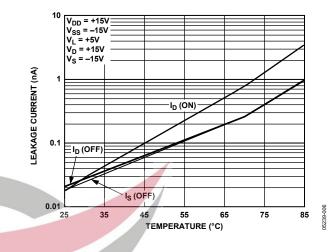


Figure 8. Leakage Currents as a Function of Temperature

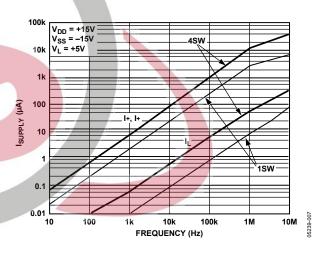


Figure 9. Supply Current vs. Input Switching Frequency

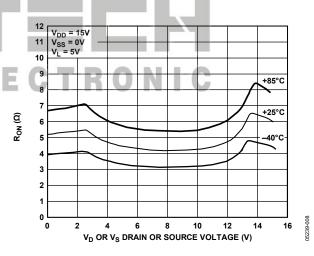
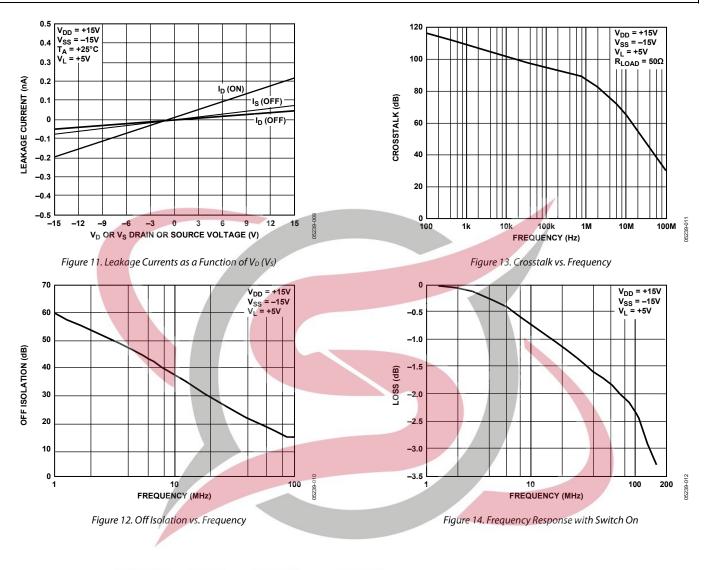


Figure 10. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures with Single Supplies

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## TERMINOLOGY

Ron

Ohmic resistance between D and S.

#### $\Delta R_{ON}$

On resistance match between any two channels, that is,  $R_{\rm ON}$  maximum minus  $R_{\rm ON}$  minimum.

#### R<sub>FLAT(ON)</sub>

Flatness is defined as the difference between the maximum and minimum value of on resistance, as measured over the specified analog signal range.

Is (OFF) Source leakage current with the switch off.

I<sub>D</sub> (**OFF**) Drain leakage current with the switch off.

I<sub>D</sub>, I<sub>s</sub> (ON) Channel leakage current with the switch on.

 $\mathbf{V}_{D}$  ( $\mathbf{V}_{s}$ ) Analog voltage on Terminal D and Terminal S.

Cs (OFF) Off switch source capacitance.

C<sub>D</sub> (OFF) Off switch drain capacitance.

#### C<sub>D</sub> (ON), C<sub>s</sub> (ON) On switch capacitance.

ton

Delay between applying the digital control input and the output switching on. See Figure 19.

toff

Delay between applying the digital control input and the output switching off.

 $t_D$ Off time or on time measured between the 90% points of both switches, when switching from one address state to another. See Figure 20.

#### Crosstalk

A measure of unwanted signal coupled through from one channel to another as a result of parasitic capacitance.

Off Isolation A measure of unwanted signal coupling through an off switch.

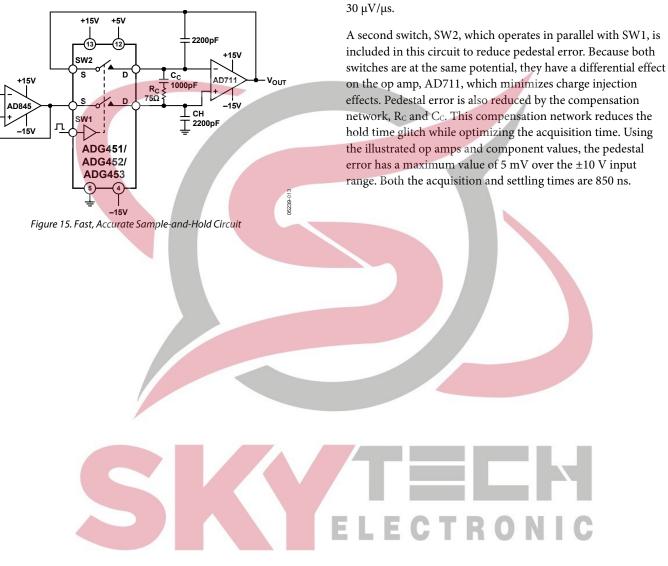
#### **Charge Injection** A measure of the glitch impulse transferred from the digital input to the analog output during switching.

# SKYTECH

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## **APPLICATIONS**

Figure 15 illustrates a precise, fast, sample-and-hold circuit. An AD845 is used as the input buffer, and the output operational amplifier is an AD711. During track mode, SW1 is closed, and the output,  $V_{OUT}$ , follows the input signal,  $V_{IN}$ . In hold mode, SW1 is opened, and the signal is held by the hold capacitor,  $C_{H}$ .



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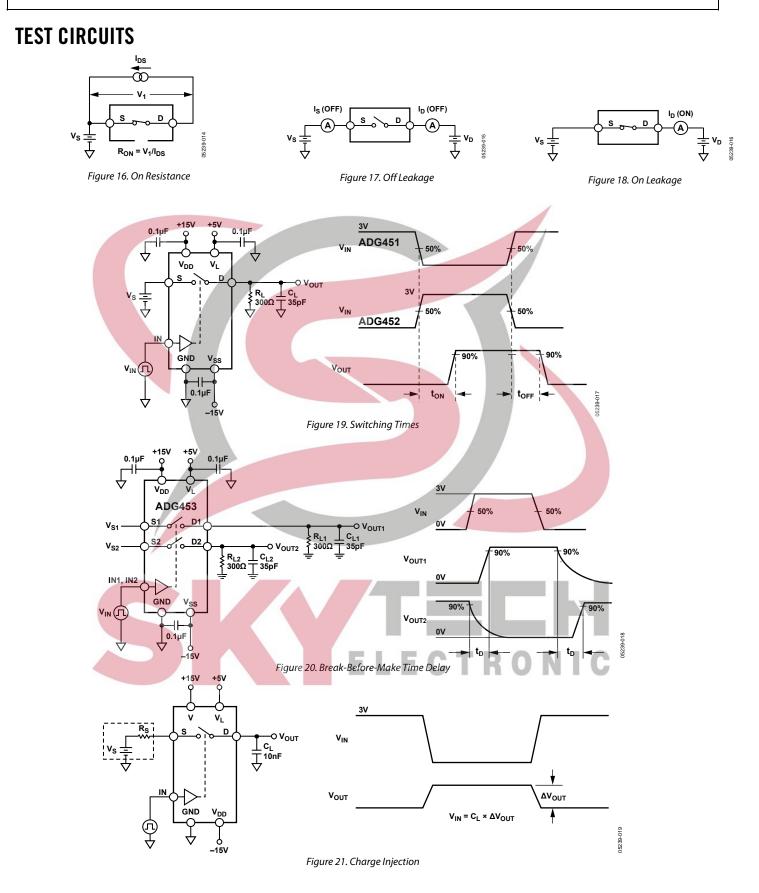
Due to switch and capacitor leakage, the voltage on the hold

droop rate is further minimized by the use of a polystyrene

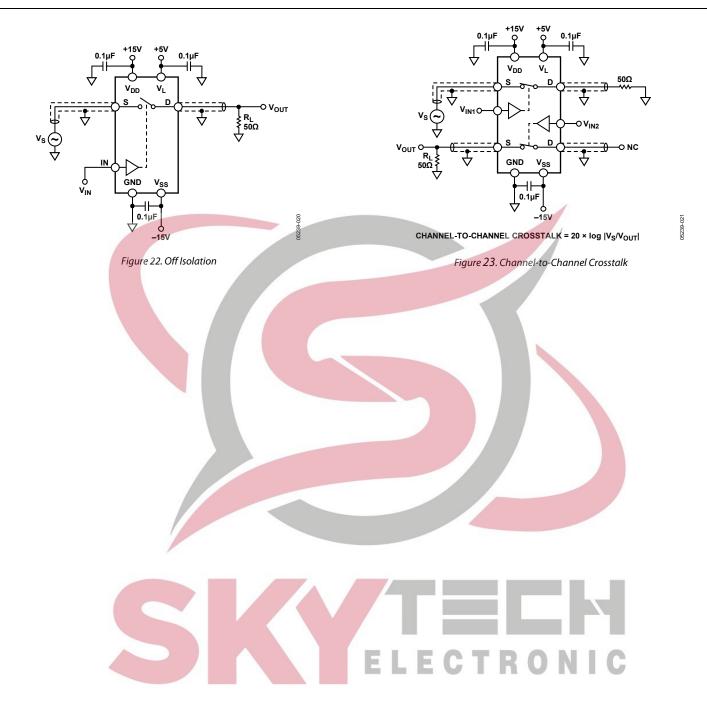
capacitor decreases with time. The ADG451/ADG452/ADG453

minimize this droop due to their low leakage specifications. The

hold capacitor. The droop rate for the circuit shown is typically

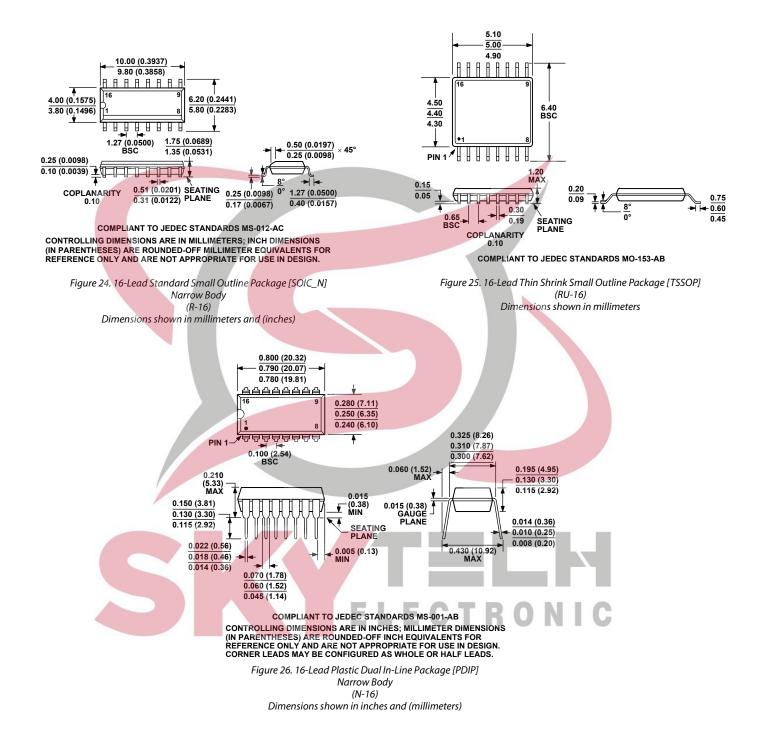


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## **OUTLINE DIMENSIONS**



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#### **ORDERING GUIDE**

Model	Temperature Range	Package Description	Package Option
ADG451BN	-40°C to +85°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG451BNZ <sup>1</sup>	-40°C to +85°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG451BR	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG451BR-REEL	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG451BR-REEL7	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG451BRZ <sup>1</sup>	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG451BRZ-REEL <sup>1</sup>	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG451BRZ-REEL7 <sup>1</sup>	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG451BRUZ <sup>1</sup>	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG451BRUZ- REEL <sup>1</sup>	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG451BRUZ- REEL71	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG451BCHIPS		DIE	
ADG452BN	-40°C to +85°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG452BNZ <sup>1</sup>	-40°C to +85°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG452BR	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG452BR-REEL	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG452BR-REEL7	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG452BRZ <sup>1</sup>	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG452BRZ-REEL <sup>1</sup>	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG452BRZ-REEL7 <sup>1</sup>	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG452BRUZ <sup>1</sup>	–40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG452BRUZ-REEL <sup>1</sup>	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG452BRUZ-REEL7 <sup>1</sup>	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG453BN	-40°C to +85°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG453BNZ <sup>1</sup>	-40°C to +85°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG453BR	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG453BR-REEL	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG453BR-REEL7	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG453BRZ <sup>1</sup>	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG453BRZ-REEL <sup>1</sup>	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG453BRZ-REEL71	-40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG453BRUZ <sup>1</sup>	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG453BRUZ-REEL <sup>1</sup>	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG453BRUZ-REEL71	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16

 $^{1}$  Z = Pb-free part.

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